

## MG1A01 GaAs Hall Element

具有高线性度与优异温度特性的砷化镓霍尔元件

Linear GaAs Hall element with excellent thermal characteristics

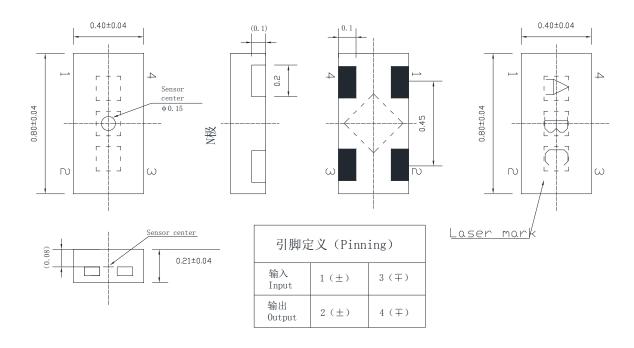
超小型 DFN 封装

Thin-type DFN Package

编带包装(每载盘 10,000 颗)

Shipped in packet-tape reel(10,000pcs per reel)

# 外形尺寸图 Dimensional Drawing (Unit: mm)



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# 绝对最大额定值 Absolute Maximum Rating

项目	符号	条件	范围	单位	
Item	Symbol	Conditions	Limit	Unit	
最大功率耗散	D		105	mW	
Maximum Power Dissipation	<b>P</b> <sub>D</sub>	<b>7</b> <sub>a</sub> = 25℃	105	IIIVV	
最大输入电压	1/		0.5	.,	
Maximum Input Voltage	<b>V</b> c		9.5	V	
工作温度	<b>T</b>		40 .125	$^{\circ}\!\mathrm{C}$	
Operating Temperature Range	<b>T</b> opr	-40 ~ +125			
保存温度	<b>T</b>		40 .450	$^{\circ}$ C	
Storage Temperature Range	<b>T</b> <sub>STG</sub>		-40 ~ +150		

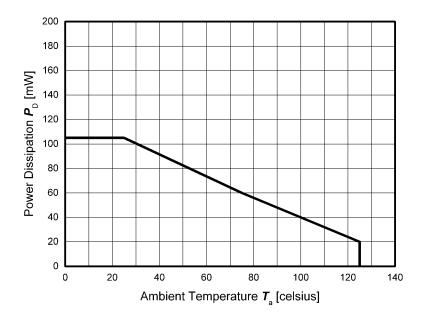


Figure 1. 最大功率耗散-环境温度

Maximum Power Dissipation  $\textbf{\textit{P}}_{D}$  as a function of ambient temperature  $\textbf{\textit{T}}_{a}$ 



## 电气特性 Electrical Characteristics (RT=25℃)

Table 1. MG1A01 电气特性表 Electrical Characteristics of MG1A01

项目	符号	测试环境		标准	最大	单位
Item	Symbol	Test Condi.	Min.	Тур.	Max.	Unit
霍尔电压	W	$B = 50 \text{mT}, I_{C} = 5 \text{mA}$	36		54	mV
Hall Voltage	<b>V</b> <sub>H</sub>	<b>7</b> <sub>a</sub> = RT				
输入电阻		$B = 0 \text{mT}, I_{C} = 0.1 \text{mA}$	650		850	Ω
Input Resist.	<b>R</b> in	<b>7</b> <sub>a</sub> = RT				
输出电阻	D	$B = 0 \text{mT}, I_{C} = 0.1 \text{mA}$	650		850	Ω
Output Resist.	<b>R</b> out	<b>7</b> <sub>a</sub> = RT				
非平衡电压	V	$B = 0mT, I_C = 5mA$	-5		+5	mV
Offset Voltage	<b>V</b> os	<b>7</b> <sub>a</sub> = RT				
霍尔电压温度系数	la 1/ l	$B = 50 \text{mT}, I_{C} = 5 \text{mA},$			0.06	% <b>/</b> ℃
Temp. Coeffi. of V <sub>H</sub>	α <b>V</b> <sub>H</sub>	<b>T</b> <sub>a</sub> =25°C ~ 125°C				
输入电阻温度系数	0	$B = 0$ mT, $I_C = 0.1$ mA,			0.3	% <b>/</b> ℃
Temp. Coeffi. of R <sub>in</sub>	α <b>R</b> in	$T_a = 25^{\circ}C \sim 125^{\circ}C$				
霍尔电压线性度	^ <b>V</b>	$B = 0.1 - 0.5T$ , $I_C = 5$ mA	-2		+2	%
Linearity of V <sub>H</sub>	∆ <b>K</b>	<b>7</b> <sub>a</sub> = RT				

Note:

1. 
$$V_{\rm H} = V_{\rm H-M} - V_{\rm os}$$

In which  $m{V}_{\text{H-M}}$  is the Output Hall Voltage,  $m{V}_{\text{H}}$  is the Hall Voltage and  $m{V}_{\text{os}}$  is the offset Voltage

under the identical electrical stimuli.

2. 
$$\alpha V_{H} = \frac{1}{V_{H}(T_{a1})} \times \frac{V_{H}(T_{a2}) - V_{H}(T_{a1})}{T_{a2} - T_{a1}} \times 100$$

$$T_{a1} = 25$$
°C,  $T_{a2} = 125$ °C

3. 
$$\alpha \mathbf{R}_{\text{in}} = \frac{1}{\mathbf{R}_{\text{in}}(\mathbf{T}_{a1})} \times \frac{\mathbf{R}_{\text{in}}(\mathbf{T}_{a2}) - \mathbf{R}_{\text{in}}(\mathbf{T}_{a1})}{\mathbf{T}_{a2} - \mathbf{T}_{a1}} \times 100$$

$$T_{a1} = 25$$
°C,  $T_{a2} = 125$ °C

4. 
$$\Delta K = \frac{K(B_1) - K(B_2)}{\frac{K(B_1) + K(B_2)}{2}} \times 100$$
  $K = \frac{V_H}{I_c \times B}$ 

$$B_1 = 0.5 \text{T}, \quad B_2 = 0.1 \text{T}$$



#### 特性曲线图 **Characteristic Curves**

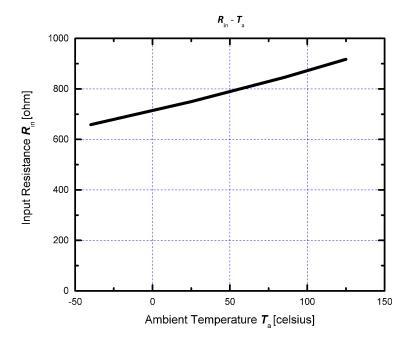


Figure 2. 输入电阻-环境温度 Input resistance  $\emph{\textbf{R}}_{in}$  as a function of ambient temperature  $\emph{\textbf{T}}_{a}$ 

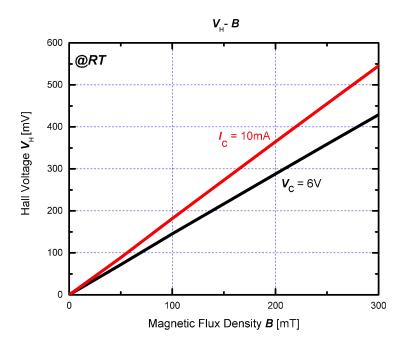


Figure 3. 霍尔电压-磁感应强度 Hall voltage  $V_H$  as a function of magnetic flux density B

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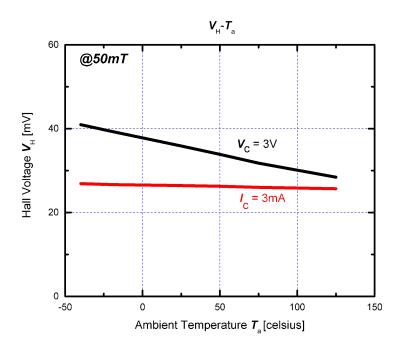


Figure 4. 霍尔电压-环境温度 Hall voltage  $V_{\rm H}$  as a function of ambient temperature  $T_{\rm a}$ 

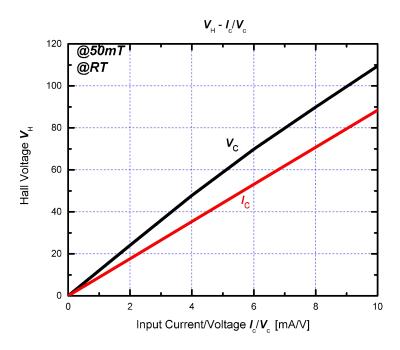


Figure 5. 霍尔电压-驱动电流/驱动电压 Hall voltage  $\emph{V}_{H}$  as a function of electrical stimuli  $\emph{I}_{c}/\emph{V}_{c}$ 



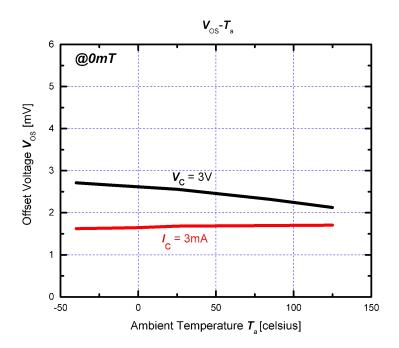


Figure 6. 非平衡电压-环境温度 Offset voltage  $V_{\mathrm{OS}}$  as a function of ambient temperature  $T_{\mathrm{a}}$ 

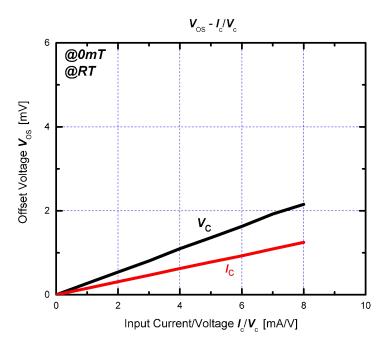


Figure 7. 非平衡电压-驱动电流/驱动电压 Offset voltage  $m{V}_{ extsf{OS}}$  as a function of electrical stimuli  $m{I}_c/m{V}_c$ 



# 焊接条件

### 助焊剂材料

- 使用树脂基助焊剂,避免使用有机或无机酸基及水溶性助焊剂。

### 助焊剂的清洗条件

- 使用乙醇或异丙醇作为清洁剂。
- 工艺温度≤50℃。
- 持续时间不超过 5 分钟。

### 焊接方法

焊接方法	焊接方法说明	焊接温度		
回流法	在高温下进行焊接的方法	最高 260℃,10 秒以内		
波峰焊	在镀锡缸中完成焊接的方法	最高 260℃,10 秒以内		
烙铁法	使用烙铁修正引脚焊接部分的方法	最高 350℃,3 秒以内		

### 焊接温度范围

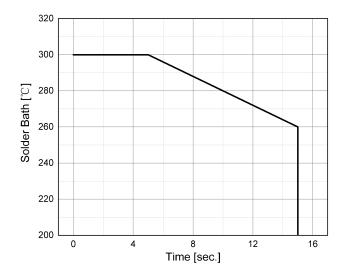


Figure 8. (参考)浸入焊接条件

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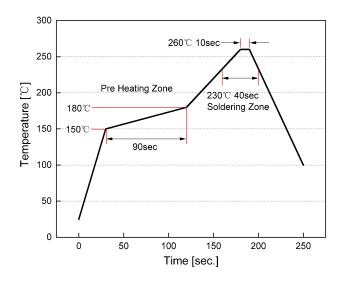


Figure 9. (参考)回流焊条件

## ESD防护

本产品对 ESD (静电放电)敏感,接触带有 ESD-Caution 标记的霍尔元件时,环境要求如下:

- 环境不太可能出现静电荷(例如,相对湿度超过 40%RH)。
- 接触产品时应该穿戴防静电服和腕带。
- 对直接接触产品的设备或容器实施防静电措施。

## 存储防护

- 产品应储存在适当的温度和湿度环境下(5至35°C,40%至85%RH),且使产品远离氯和腐蚀性气体。
- 即使在适当的条件下,长期存放也可能导致产品的可焊接性和电气性能降低。针对长期存放的产品,应 该在使用前应检查其可焊性。
- 如果储存超过 2 年,建议储存在氮气环境中。大气中的氧气会氧化产品的引线,导致引线可焊接性变差。

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# 安全防护

- 请勿通过燃烧,粉碎或化学处理等方式将本产品变成气体,粉末或液体。
- 丢弃本产品时,请遵守法律和公司规定。



## **Soldering Conditions**

The following conditions should be preserved. Solder ability should be checked by yourself, because it is depend on solder paste material and other parameters.

#### Material of solder flux

- Use the resin based flux and refrain from using organic or inorganic acid based and water-soluble one.

## Cleansing of solder flux conditions

- Use Ethanol or Isopropyl alcohol as cleansing material.
- Process temperature should be 50°C or less.
- Duration should be 5min or less.

### Hand-Soldering

 Solder the leads to PC board at the point(part from the body) at 260°C for 10 seconds or 350°C for less than 3 seconds.

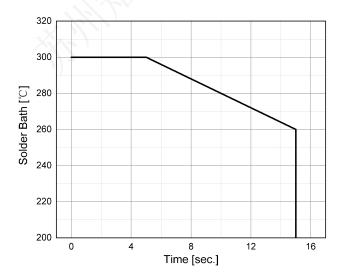


Figure 8. (Reference) Conditions of Dip Soldering

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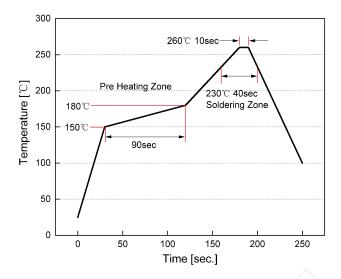


Figure 9. (Reference) Conditions of Reflow Profile

## **Precautions for ESD**

This product is the device that is sensitive to ESD (Electrostatic Discharge). Handling Hall Elements with the ESD-Caution mark under the environment in which

- Static electrical charge is unlikely to arise. (Ex; Relative Humidity; over 40% RH).
- Wearing the antistatic suit and wristband when handling the devices.
- Implementing measures against ESD as for containers that directly touch the devices.

## **Precautions for Storage**

- Products should be stored at an appropriate temperature and humidity (5 to 35°C, 40 to 85%RH).
  Keep products away from chlorine and corrosive gas.
- Long-term storage may result in poor lead solder ability and degraded electrical performance even
  under proper conditions. For those parts, which stored long –term shall be check solder ability before it

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is used.

 For storage longer than 2 years, it is recommended to store in nitrogen atmosphere. Oxygen of atmosphere oxidizes leads of products and lead solder ability get worse.

# **Precautions for Safety**

- Do not alter the form of this product into a gas, powder or liquid through burning, crushing or chemical processing.
- Observe laws and company regulations when discarding this product.